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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω) TYP.	I _D (A)	Q _g (TYP.)			
100	0.0032 at V _{GS} = 10 V	180	53.5 nC			
100	0.0039 at V _{GS} = 7.5 V	159	33.3 110			

D²PAK (TO-263)

N-Channel MOSFET

FEATURES

- Maximum 175 °C junction temperature
- \bullet 100 % R_g and UIS tested



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS (7	$\Gamma_{\rm C}$ = 25 °C, unless othe	rwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T. 150 °C)	T _C = 25 °C		180	
Continuous Drain Current (T _J = 150 °C)	T _C = 125 °C	I _D	90	_
Pulsed Drain Current (t = 100 μs)		I _{DM}	700	A .
Avalanche Current	L = 0.1 mH	I _{AS}	50	
Single Avalanche Energy ^a	L = U.1 MH	E _{AS}	1238	mJ
Maximum Dawar Dissipation 3	T _C = 25 °C	В	375 ^b	w
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	125 ^b	T VV
Operating Junction and Storage Temperature Ra	ınge	T _J , T _{stq}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{thJC}	0.75	C/VV		

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.

Top View

c. When mounted on 1" square PCB (FR4 material).



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	1						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	_	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	μA	
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 175 ^{\circ}\text{C}$	-	-	2	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	90	-	-	Α	
Drain Source On State Begintenes 3	D-	V _{GS} = 10 V, I _D = 30 A	-	0.0032	0.0039	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 20 \text{ A}$	-	0.0039	0.0042		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$	-	85	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	3330	-	pF	
Output Capacitance	C _{oss}		-	1395	-		
Reverse Transfer Capacitance	C _{rss}		-	95	-		
Total Gate Charge ^c	Q_g		-	53.5	81	nC	
Gate-Source Charge ^c	Q _{gs}	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 30 A	-	14.5	-		
Gate-Drain Charge ^c	Q_{gd}		-	13.2	-		
Gate Resistance	R_g	f = 1 MHz	0.9	1.9	3.8	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	13	26		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 1.67 \Omega$	-	22	44	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong 30$ A, $V_{GEN}=10$ V, $R_g=1~\Omega$	-	27	54		
Fall Time ^c	t _f		-	9	18		
Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	700	Α	
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V	-	0.86	1.4	V	
Reverse Recovery Time	t _{rr}		-	88	176	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	10	Α	
Reverse Recovery Charge	Q _{rr}		-	0.22	0.44	μC	

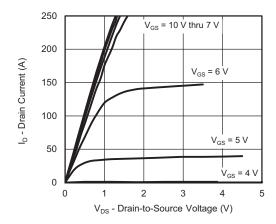
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

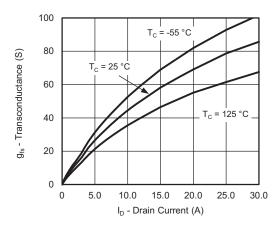
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



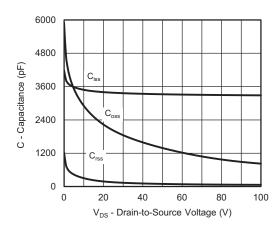
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



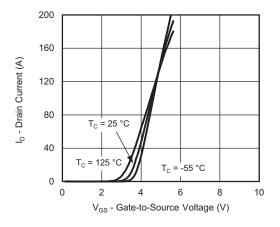
Output Characteristics



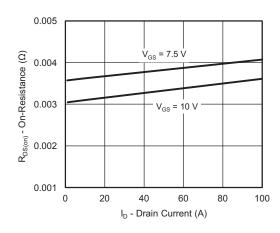
Transconductance



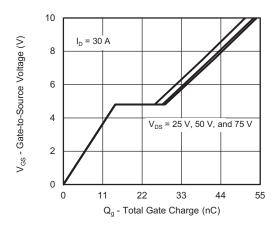
Capacitance



Transfer Characteristics



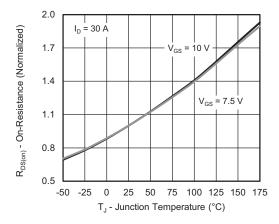
On-Resistance vs. Drain Current



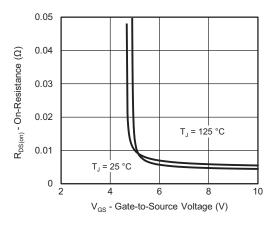
Gate Charge



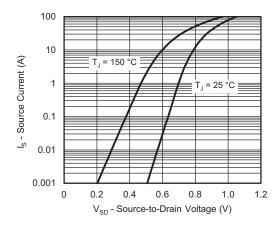
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



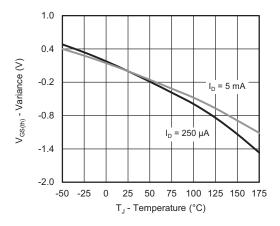
On-Resistance vs. Junction Temperature



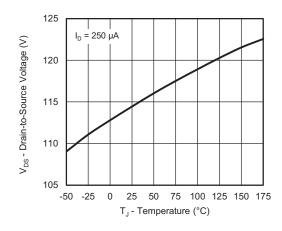
On-Resistance vs. Gate-to-Source Voltage



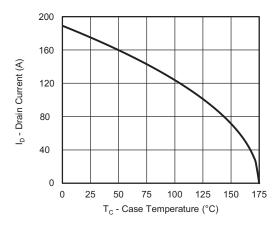
Source Drain Diode Forward Voltage



Threshold Voltage



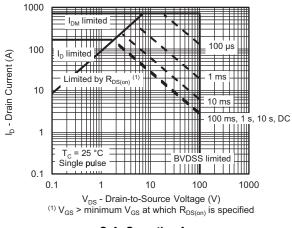
Drain Source Breakdown vs. Junction Temperature

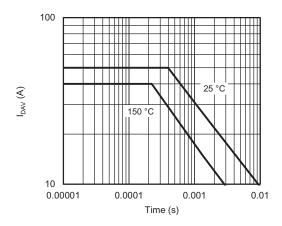


Current De-Rating



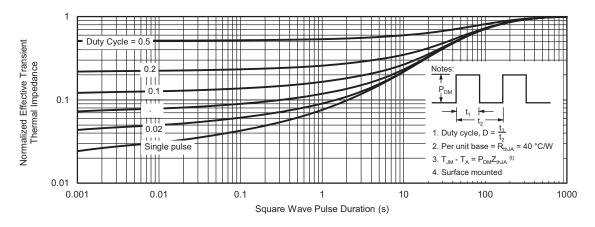
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)





Safe Operating Area

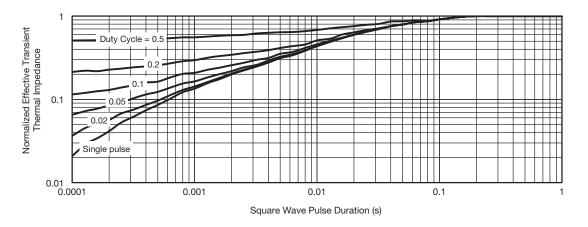
 I_{DAV} vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



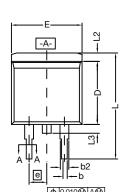
Normalized Thermal Transient Impedance, Junction-to-Case

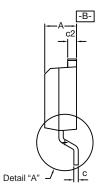
Note

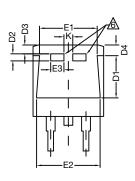
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-263 (D²PAK): 3-LEAD

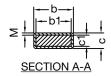








DETAIL A (ROTATED 90°)



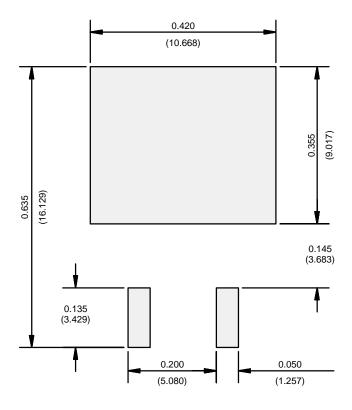
		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
b		0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
D1		0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829 1.981		
	е	0.100 BSC		2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254	BSC	
	М	-	0.002	-	0.050	

ECN: T13-0707-Rev. K, 30-Sep-13

DWG: 5843

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.
 6. This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D2PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)





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